

Supplementary Materials



GABr Post-Treatment for High-Performance MAPbI₃ Solar Cells on Rigid Glass and Flexible Substrate

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Figure S1. *J-V* curves of devices treated by high concentration of GABr measured under different scan directions.

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Figure S2. (a) SEM image of 8 mg·ml⁻¹ GABr treated MAPbI₃ and (b) the cross-sectional SEM image of 8 mg·mL⁻¹ GABr treated solar cell device.







Figure S4. SEM images of (a) MAPbI3 and (b) GABr treated MAPbI3 deposited on flexible substrates.



Figure S5. The transmittance spectra for both substrates for rigid and flexible devices.

Table S1, H	I values of dev	ices treated by	v different d	concentrations (of GABr
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x value	0	1	2	3	4	5	6	7	8	10
HI (%)	30.49	29.9	11.08	5.25	2.46	13.29	17.36	19.63	19.19	28.42

Atomic Ratio of Elements (%)				
Reference	GABr			
66.69	68.34			
26.18	25.65			
5.58	3.37			
1.55	2.50			
0	0.14			
	Atomic Ratio of Elem Reference 66.69 26.18 5.58 1.55 0			

Table S2. Atomic ratio of MAPbI3 and GABr-treated film obtained from XPS data.

Table S3. J-V parameters of the champion devices based on MAPbI $_3$ and GABr-treated MAPbI $_3$ on rigid substrates.

Sample	Jsc (mA/cm ²)	<i>V</i> oc (V)	FF (%)	PCE (%)
reference-forward	23.26	1.041	56.24	13.62
reference-reverse	22.93	1.055	74.21	17.95
GABr-forward	23.39	1.132	69.03	18.27
GABr-reverse	23.06	1.130	76.81	20.01

Table S4. *J-V* parameters and HI values of the champion devices based on MAPbI₃ and GABrtreated MAPbI₃ on flexible substrates.

Sample	Jsc (mA/cm ²)	<i>V</i> oc (V)	FF (%)	PCE (%)	HI (%)	
reference-forward	22.11	1.041	49.36	11.36	27.06	
reference-reverse	21.29	1.055	70.21	15.77	27.96	
GABr-forward	22.0	1.078	64.43	15.28	12.02	
GABr-reverse	21.71	1.09	74.25	17.57	13.03	